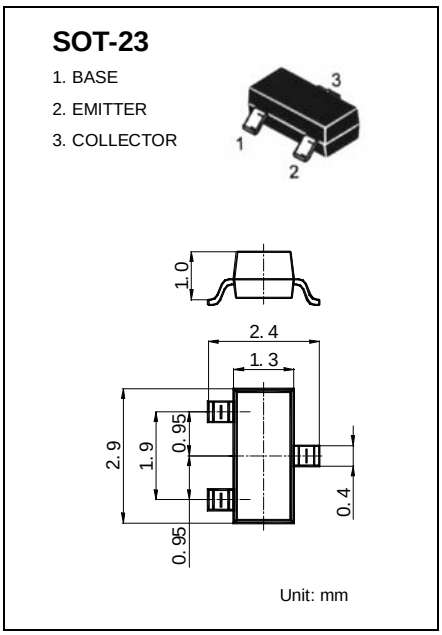
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Transistors

MMBT5550LT1 TRANSISTOR (NPN)



FEATURES

Power dissipation

P_{CM}: 0.225 W (Tamb=25℃)

Collector current

I_{CM}: 0.6 A

Collector-base voltage

$V_{(BR)CBO}$: 160 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic= 100μA, I_E=0	160		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic= 1 mA, I_B=0	140		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= 10μA, I_C=0	6		V
Collector cut-off current	I_{CBO}	V_{CB}=100V, I_E=0		0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 4V, I_C=0		0.05	μA
DC current gain	$h_{FE(1)}$	V_{CE}= 5V, I_C= 1mA	60		
	$h_{FE(2)}$	V_{CE}= 5V, I_C=10mA	60	250	
	$h_{FE(3)}$	V_{CE}= 5V, I_C=50mA	20		
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=10 mA, I_B=1mA		0.15	V
		I_C=50 mA, I_B= 5mA		0.25	
Base-emitter saturation voltage	V_{BE}(sat)	I_C=10 mA, I_B= 1mA		1	V
		I_C=50 mA, I_B= 5mA		1.2	
Transition frequency	f_T	V_{CE}= 10V, I_C= 10mA,f=100MHz	100		MHz
Output capacitance	C_{ob}	V_{CE}=10V, I_E=0, f=1MHz		6	pF

DEVICE MARKING

MMBT5550LT1=M1F